What is claimed is:

| 13 | 2 |
|----|---|
| | X |

- The solid diamond electron emitter of claim 18 wherein said point has a surface roughness below about 10 angstroms.
- 3 8) The solid diamond electron emitter of claim 48 wherein said radius is less than about 10μm.
- Y (2) The solid diamond electron emitter of claim 18 wherein said radius ranges form about 3 angstroms to about 3 μm.

The solid diamond electron emitter of claim 18 further including a conductive shank to which said diamond is adhered.

11) The solid diamond electron emitter of claim 10 wherein said diamond is adhered to said conductive shank by a vapor deposited layer of palladium or titanium.

7 12) The solid diamond field emitter of claim 10 wherein said radius is less than about 10 μ m.

84

The solid diamond electron emitter of claim 10 wherein said radius ranges from about 3 angstroms to about 3 μm.

Clean Copy

14) The solid diamond electron field emitter of claim 10 wherein said point is produced using a non-contact machining technique.

5

15) The solid diamond electron emitter of claim 14 wherein said noncontact machining technique is selected from the group consisting of electron beam, ion beam and laser machining techniques.

10

A solid diamond electron emitter comprising a diamond greater than 5μm in thickness having a pointed surface with a radius of less than about 100μm, said pointed surface having a roughness of between about 20 angstroms and about 10μm.

15

20

A field emitter extractor gauge comprising a field emitter array, an anode grid, a focus plate, a reflector and a collector wherein said field emitter array comprises an array of solid diamond electron emitters each comprising a diamond greater than 5μm in thickness having a pointed surface with a radius of less than about 100μm, said pointed surface having a roughness of between about 20 angstroms and about 10μm.